

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

48
papers

916
citations

17
h-index

28
g-index

49
ext. papers

1,056
ext. citations

2.6
avg, IF

3.76
L-index

#	Paper	IF	Citations
48	Review of radiation damage in GaN-based materials and devices. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2013 , 31, 050801	2.9	145
47	Radiation effects in GaN materials and devices. <i>Journal of Materials Chemistry C</i> , 2013 , 1, 877-887	7.1	139
46	Isolation blocking voltage of nitrogen ion-implanted AlGaIn/GaN high electron mobility transistor structure. <i>Applied Physics Letters</i> , 2010 , 97, 262116	3.4	43
45	Functionalization with MXene (Ti ₃ C ₂) Enhances the Wettability and Shear Strength of Carbon Fiber-Epoxy Composites. <i>ACS Applied Nano Materials</i> , 2019 , 2, 5553-5562	5.6	35
44	Characterization of the gate oxide of an AlGaIn/GaN high electron mobility transistor. <i>Applied Physics Letters</i> , 2011 , 98, 122103	3.4	30
43	Investigation of the effect of temperature during off-state degradation of AlGaIn/GaN High Electron Mobility Transistors. <i>Microelectronics Reliability</i> , 2012 , 52, 23-28	1.2	29
42	Dependence on proton energy of degradation of AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 022201	1.3	29
41	Degradation Mechanisms for GaN and GaAs High Speed Transistors. <i>Materials</i> , 2012 , 5, 2498-2520	3.5	29
40	Comparison of neutron irradiation effects in AlGaIn/AlN/GaN, AlGaIn/GaN, and InAlN/GaN heterojunctions. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012 , 30, 061207	1.3	28
39	Modeling Proton Irradiation in AlGaIn/GaN HEMTs: Understanding the Increase of Critical Voltage. <i>IEEE Transactions on Nuclear Science</i> , 2013 , 60, 4103-4108	1.7	25
38	Three-Dimensional Porous TiO ₂ -NiO Composite Electrodes with Enhanced Electrochemical Performance for Supercapacitors. <i>Materials</i> , 2019 , 12,	3.5	25
37	Effects of proton irradiation energies on degradation of AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012 , 30, 012202	1.3	24
36	Effect of source field plate on the characteristics of off-state, step-stressed AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011 , 29, 032204	1.3	23
35	Impact of proton irradiation on dc performance of AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 042202	1.3	20
34	Effect of electron irradiation on AlGaIn/GaN and InAlN/GaN heterojunctions. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 022206	1.3	19
33	Improvement of Off-State Stress Critical Voltage by Using Pt-Gated AlGaIn/GaN High Electron Mobility Transistors. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H264		19
32	Inkjet Printing Transparent and Conductive MXene (TiC) Films: A Strategy for Flexible Energy Storage Devices. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 17766-17780	9.5	19

31	Effects of proton irradiation on dc characteristics of InAlN/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2011 , 29, 061201	1.3	17
30	Effect of temperature on CO sensing response in air ambient by using ZnO nanorod-gated AlGaIn/GaN high electron mobility transistors. <i>Sensors and Actuators B: Chemical</i> , 2013 , 176, 708-712	8.5	16
29	Effect of buffer structures on AlGaIn/GaN high electron mobility transistor reliability. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2013 , 31, 011805	1.3	16
28	Annealing temperature dependence of Ohmic contact resistance and morphology on InAlN/GaN high electron mobility transistor structures. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2011 , 29, 021002	1.3	14
27	Effect of buffer layer structure on electrical and structural properties of AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2012 , 30, 011205	1.3	13
26	Study on the effects of proton irradiation on the dc characteristics of AlGaIn/GaN high electron mobility transistors with source field plate. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2014 , 32, 022202	1.3	12
25	Transmission electron microscopy characterization of electrically stressed AlGaIn/GaN high electron mobility transistor devices. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2012 , 30, 062204	1.3	12
24	Under-gate defect formation in Ni-gate AlGaIn/GaN high electron mobility transistors. <i>Microelectronics Reliability</i> , 2012 , 52, 2542-2546	1.2	11
23	Comparison of passivation layers for AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2011 , 29, 061204	1.3	11
22	Investigating the effect of off-state stress on trap densities in AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2011 , 29, 060603	1.3	11
21	Electrical characterization of ⁶⁰ Co gamma radiation-exposed InAlN/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2013 , 31, 051210	1.3	10
20	Proton irradiation energy dependence of dc and rf characteristics on InAlN/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2012 , 30, 041206	1.3	9
19	Effects of 2 MeV Ge ⁺ irradiation on AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2013 , 31, 021205	1.3	8
18	Circular and rectangular via holes formed in SiC via using ArF based UV excimer laser. <i>Applied Surface Science</i> , 2011 , 257, 2303-2307	6.7	8
17	Effects of silicon nitride passivation on isolation-blocking voltage in algan/gan high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2011 , 29, 031211	1.3	8
16	Carbon monoxide detection sensitivity of ZnO nanorod-gated AlGaIn/GaN high electron mobility transistors in different temperature environments. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2012 , 30, 010606	1.3	7
15	Construction of biomimetic artificial intervertebral disc scaffold via 3D printing and electrospinning. <i>Materials Science and Engineering C</i> , 2021 , 128, 112310	8.3	7
14	Methane detection using Pt-gated AlGaIn/GaN high electron mobility transistor based Schottky diodes. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2013 , 31, 032203	1.3	6

13	Thermal simulation of laser lift-off AlGaIn/GaN high electron mobility transistors mounted on AlN substrates. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2011 , 29, 041202	1.3	6
12	Degradation of dc characteristics of InAlN/GaN high electron mobility transistors by 5 MeV proton irradiation. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2012 , 30, 031202	1.3	5
11	MXene (TiCT) Functionalized Short Carbon Fibers as a Cross-Scale Mechanical Reinforcement for Epoxy Composites. <i>Polymers</i> , 2021 , 13,	4.5	5
10	PVdF-HFP-Based Gel Polymer Electrolyte with Semi-Interpenetrating Networks For Dendrite-Free Lithium Metal Battery. <i>Acta Metallurgica Sinica (English Letters)</i> , 2021 , 34, 417-424	2.5	5
9	Effect of Drain Bias on Degradation of AlGaIn/GaN High Electron Mobility Transistors under X-Band Operation. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H464		4
8	Radiation Damage in GaN-Based Materials and Devices 2014 , 345-387		3
7	193 nm excimer laser lift-off for AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2012 , 30, 051209	1.3	3
6	Comparison of DC performance of Pt/Ti/Au- and Ni/Au-gated AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2011 , 29, 042202	1.3	3
5	Attapulgite-MXene Hybrids with TiCT Lamellae Surface Modified by Attapulgite as a Mechanical Reinforcement for Epoxy Composites. <i>Polymers</i> , 2021 , 13,	4.5	3
4	Radiation Damage in GaN-Based Materials and Devices 2013 , 1753-1764		1
3	Radiation Damage in GaN-Based Materials and Devices 2013 , 1753-1764		1
2	Mechanical properties of phase-pure bulk Ta ₄ AlC ₃ prepared by spark plasma sintering and subsequent heat treatment. <i>Processing and Application of Ceramics</i> , 2021 , 15, 211-218	1.4	0
1	Flexible and High-Performance MXene/MnO ₂ Film Electrodes Fabricated by Inkjet Printing: Toward a New Generation Supercapacitive Application (Adv. Mater. Interfaces 21/2021). <i>Advanced Materials Interfaces</i> , 2021 , 8, 2170117	4.6	